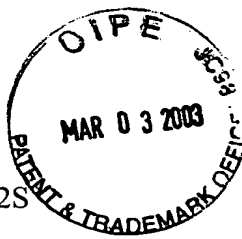


DOCKET NO.: 214258US2S



#15  
Amdt  
a  
3/12/03  
arg

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
MICHIHARU MATSUI ET AL : EXAMINER: TRAN, T. F.  
SERIAL NO: 09/956,986 :  
FILED: SEPTEMBER 21, 2001 : GROUP ART UNIT: 2811  
FOR: NONVOLATILE :  
SEMICONDUCTOR MEMORY :  
DEVICE HAVING ELEMENT :  
ISOLATING REGION OF TRENCH :  
TYPE AND METHOD OF :  
MANUFACTURING THE SAME :

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Official Action mailed December 3, 2002, please amend this  
application as follows:

IN THE CLAIMS

Please amend Claims 1, 3, 5, 32, 34 and 36 to read as follows:<sup>1</sup>

1. A semiconductor device comprising:
- a semiconductor layer;
  - a first insulating film formed on said semiconductor layer;
  - a first electrode layer formed on said first insulating film;
  - an element isolating region comprising an element isolating insulating film formed to extend through said first electrode layer and said first insulating film to reach an inner region

RECEIVED  
MAR - 6 2003  
TECHNOLOGY CENTER 2800

03/04/2003 ANABT1 00000050 09956986 36.00 0P  
2021:01 10

A  
B3